

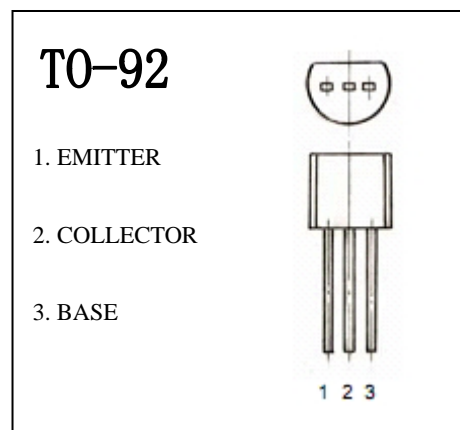
深圳市晶泰源电子有限公司

2SC1923

TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	40	V
VCEO	Collector-Emitter Voltage	30	V
VEBO	Emitter-Base Voltage	4	V
IC	Collector Current	0.02	A
PC	Collector Power Dissipation	100	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =100uA, I _E =0	40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =1mA, I _B =0	30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _C =100uA, I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μA
DC current gain	H _{FE}	V _{ce} =6V, I _c =1mA	40		200	
Reverse Transfer Capacitance	C _{re}	V _{CE} =6V, f=1MHZ		0.70		PF
Transition frequency	f _T	V _{CE} =6V, I _C =1mA, f=100MHZ		550		MHz
Collector output capacitance	C _{ob}	V _{CB} =6V, I _E =-1mA, f=30MHz			30	ps
Noise Figure	NF	V _{CE} =6V, I _E =-1mA, f=100MHZ		2.5	4.0	dB
Power Gain	G _{pe}		15	18		